

Multi-layer THGEM (M-THGEM) for hadron calorimeter and muon system

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Outline

- HCAL and Muon system of CEPC
- THGEM development
- M-THGEM
- Summary

HCAL and Muon system of CEPC

CEPC

A high-luminosity circular e^+e^- collider and clean Higgs and/or Z factory proposed in China.

Center-of-mass energy: $\sqrt{s} \sim 240$ GeV

Luminosity: $L \sim 2 \times 10^{34}$ cm $^{-2}$ s $^{-1}$

HCAL

A high-granularity sampling calorimeter with steel as the absorber and sensitive devices, such as scintillator tiles or gaseous detectors .

Energy resolution: $50\% \sqrt{E(\text{GeV})}$

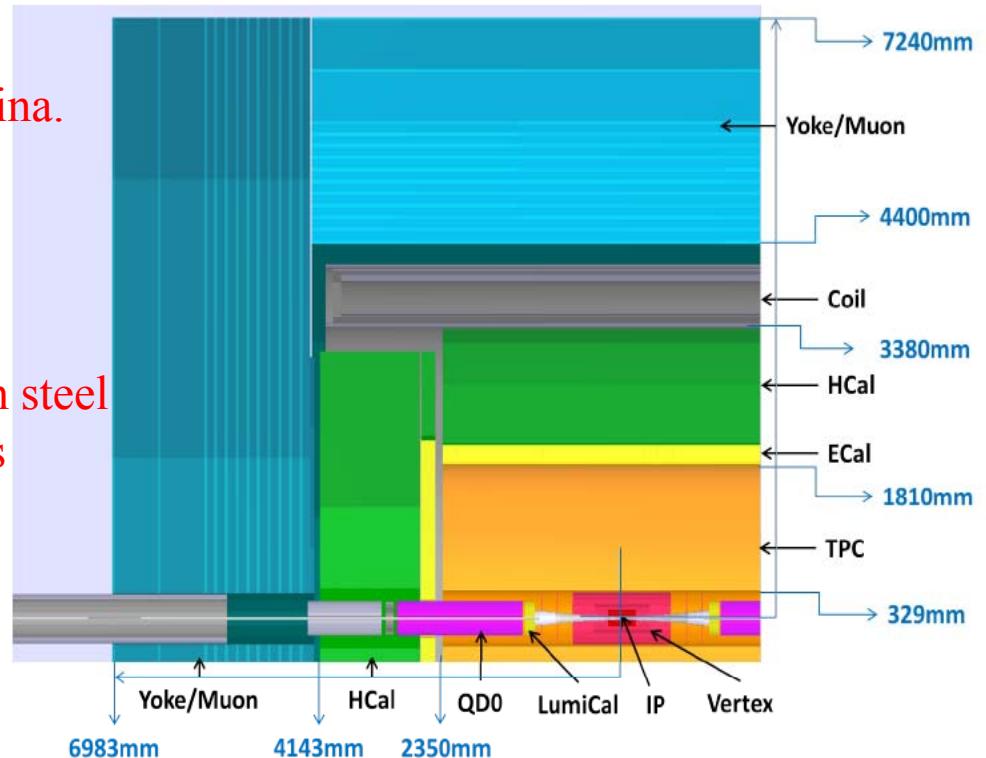
Jet energy resolution, ECAL+HCAL+PFA:
 $\sigma E/E = 3 - 4\%$, or $30\% \sqrt{E(\text{GeV})}$ @100GeV

Muon system

A high-efficiency and low-cost tracking detector with steel as the absorber and sensitive devices, such as scintillator tiles or gaseous detectors

Reconstruction efficiency: 94%

$P(\pi \rightarrow \mu)@30 \text{ GeV} < 1\%$



CEPC detector overview (baseline)

The HCAL and Muon system have similar options for sensitive detector, and one detection technology may be adopted for both systems!

Hadronic calorimeter

Options

- Analog HCAL
- Digital HCAL
- Semi-digital HCAL
- Dual-readout HCAL

Detector requirements

Granularity: $1 \times 1 \text{ cm}^2$ or $3 \times 3 \text{ cm}^2$

Readout channel density: $\sim 4 \times 10^5 / \text{m}^3$

Total volume: 100 m^3

Layers: ~ 40

Thickness/layer: $\sim 6\text{mm}$

High rate: $>1\text{kHz/cm}^2$

High performance-price ratio

Technologies

Scintillator detector

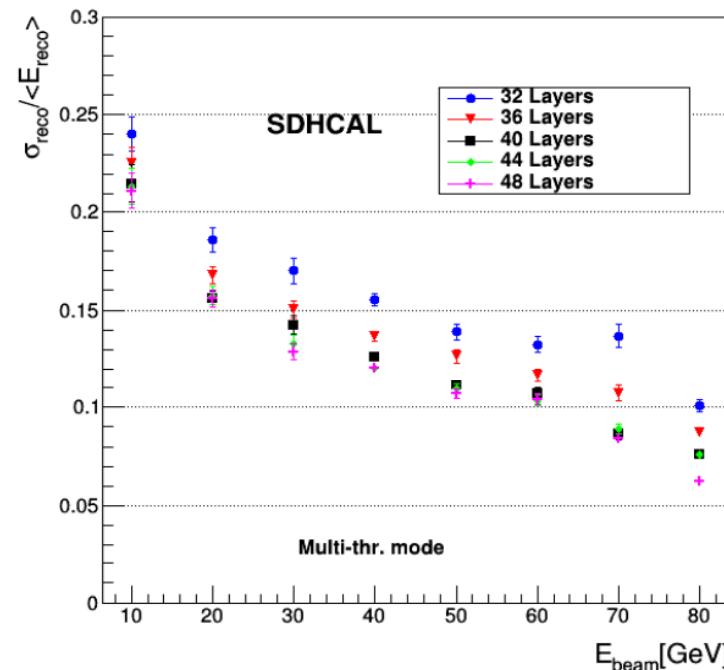
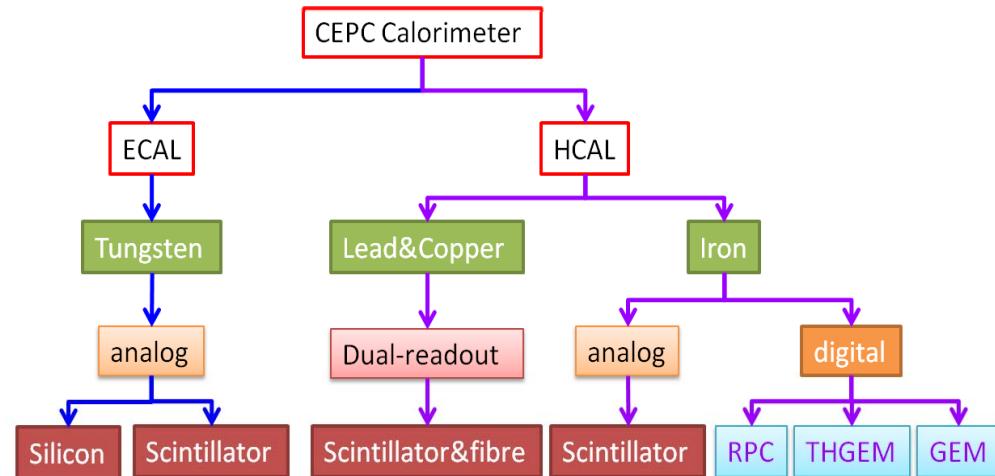
Plastic scintillator + SiPM

Gas detector

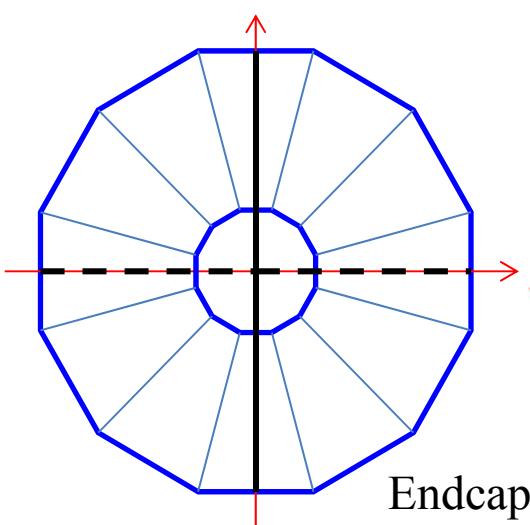
RPC (Glass RPC, Bakelite RPC)

GEM (CERN type GEM)

THGEM (new structure THGEMs) ...



Muon system



Options

No dependent muon system

Good muon system

Detector requirements

Spatial resolution: ≤ 2 cm

Detection efficiency: 95%

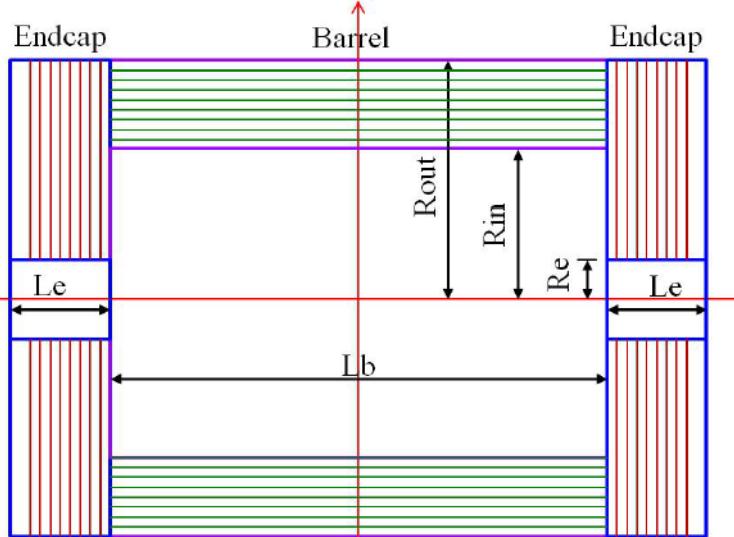
Layers: ~8

Thickness/layer: <4cm

High rate: >60 Hz/cm²

Total area: ~9000 m²

Low cost, good stability, long-lived, easy mass production



Technologies

Scintillator detector

Scintillator strip + SiPM (1cm-thick)

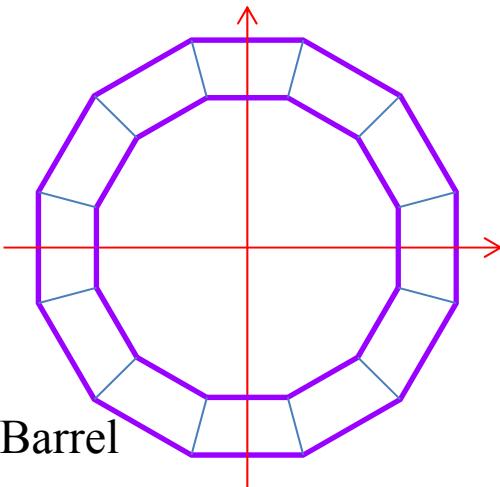
Gas detector

RPC (Glass RPC, Bakelite RPC)

μ RWell

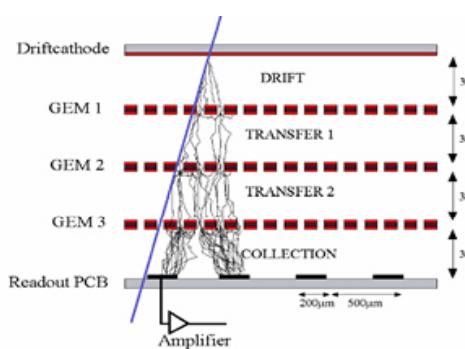
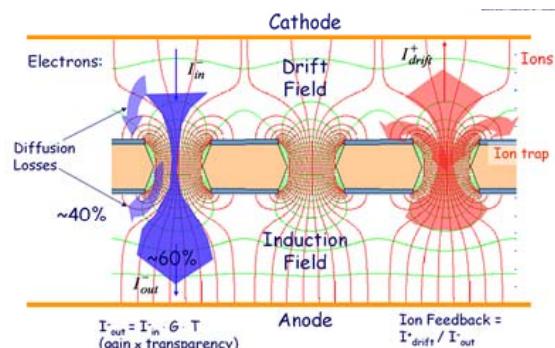
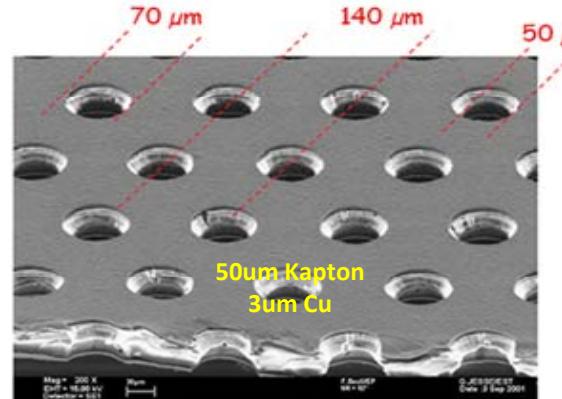
THGEM (new structure THGEMs)

Dodecagon segments



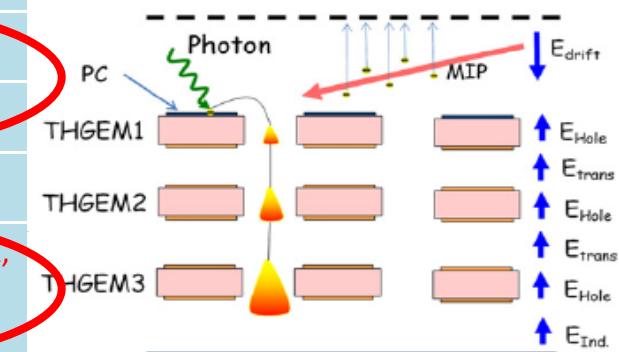
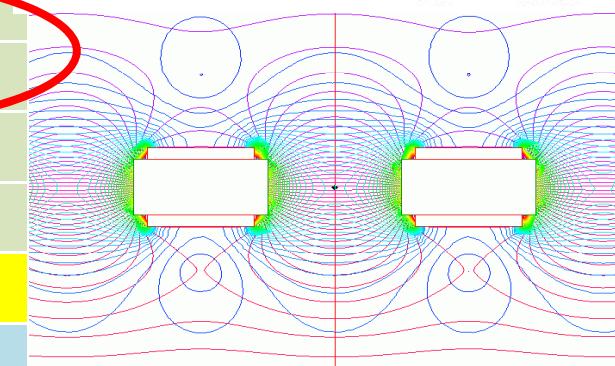
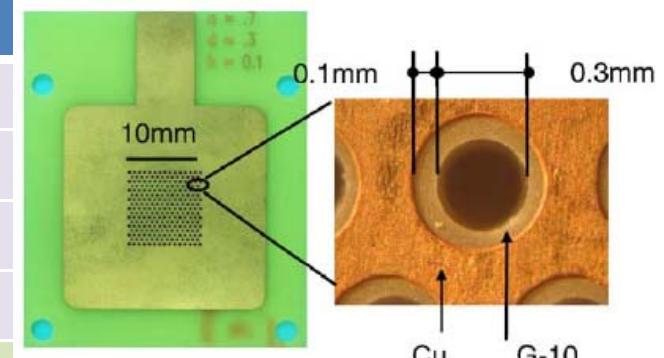
THGEM development

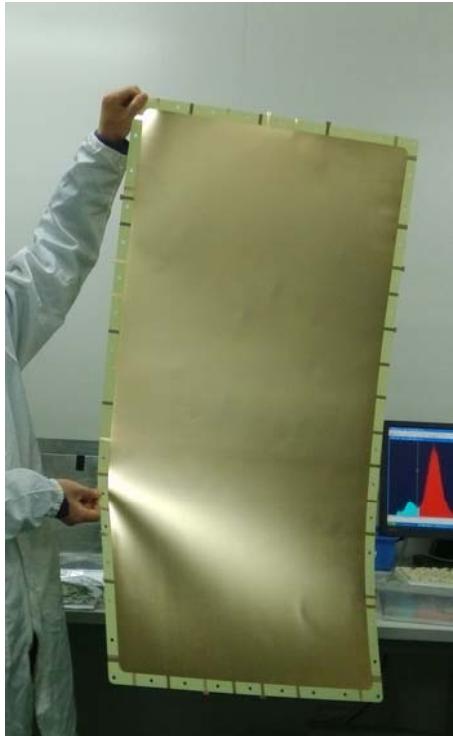
GEM(Gas Electron Multiplier), 1997 by F. Sauli



→ THGEM(Thick GEM), 2004 by A. Breskin

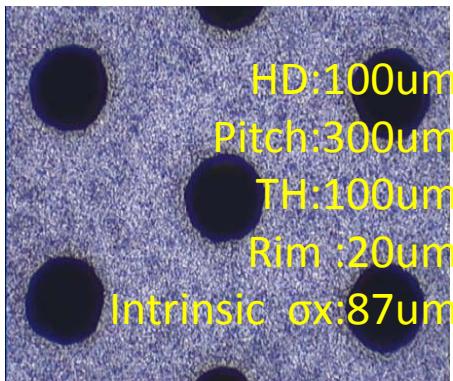
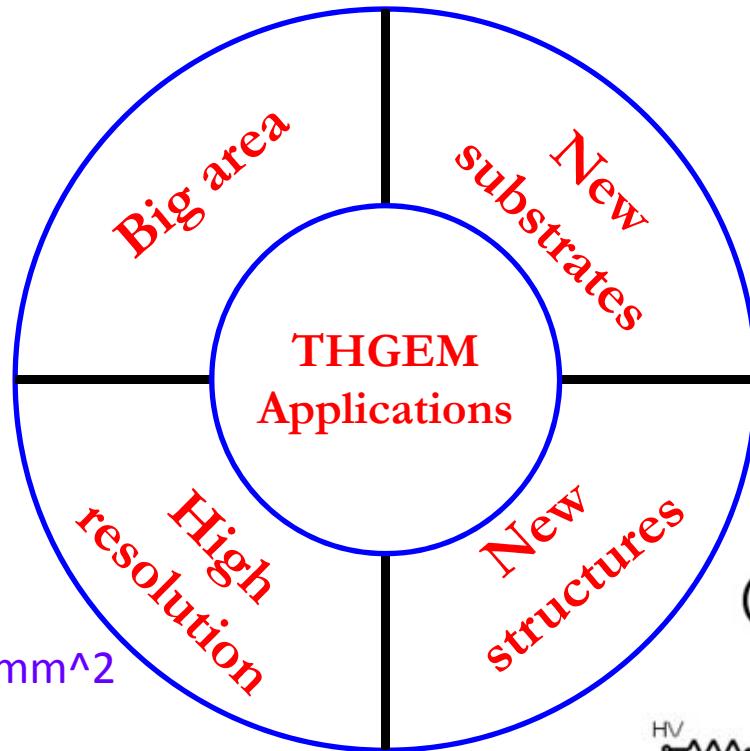
| GEM | 项目 | THGEM |
|-------------|-------------------|-----------------------------|
| 50 | T/um | >=200 |
| 70 | D/um | >=200 |
| 140 | P/um | >=500 |
| 10 | Rim/u | >=20 |
| $\sim 10^3$ | GainS | $>=10^4$ |
| $\sim 10^4$ | GainD | $>=10^5$ |
| <20% | $\sigma E(FWHM)S$ | ~20% |
| ~25% | $\sigma E(FWHM)D$ | ~30% |
| <100u | σX | <500u |
| High | Tech | Normal |
| Gain | Cost | Low |
| Fragile | Durability | Robust |
| Good | Stability | +++ |
| Kapton | Substrates | FR-4, PTFE, Ceramic, Kapton |



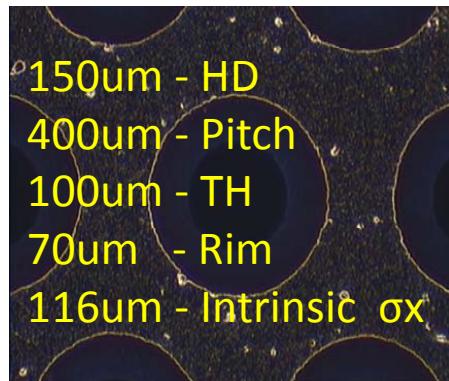


100×100 200×200
300×300 400×400
500×500 500×1000 mm²

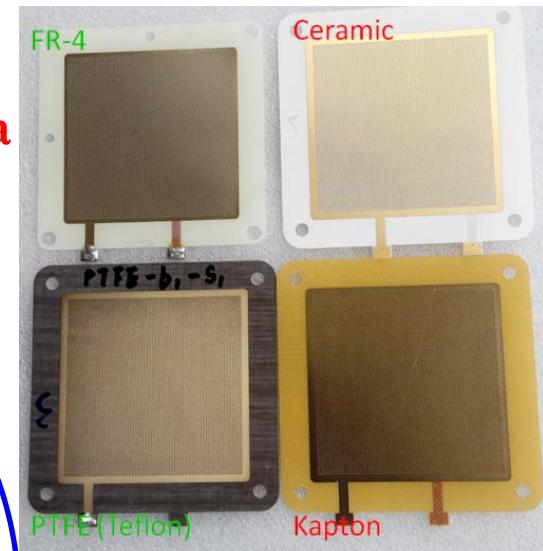
Developed by IHEP and
KingBrother Co. Ltd. in China



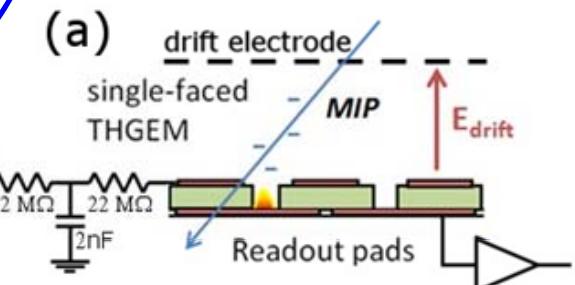
HD:100um
Pitch:300um
TH:100um
Rim :20um
Intrinsic σ :87um



150um - HD
400um - Pitch
100um - TH
70um - Rim
116um - Intrinsic σ

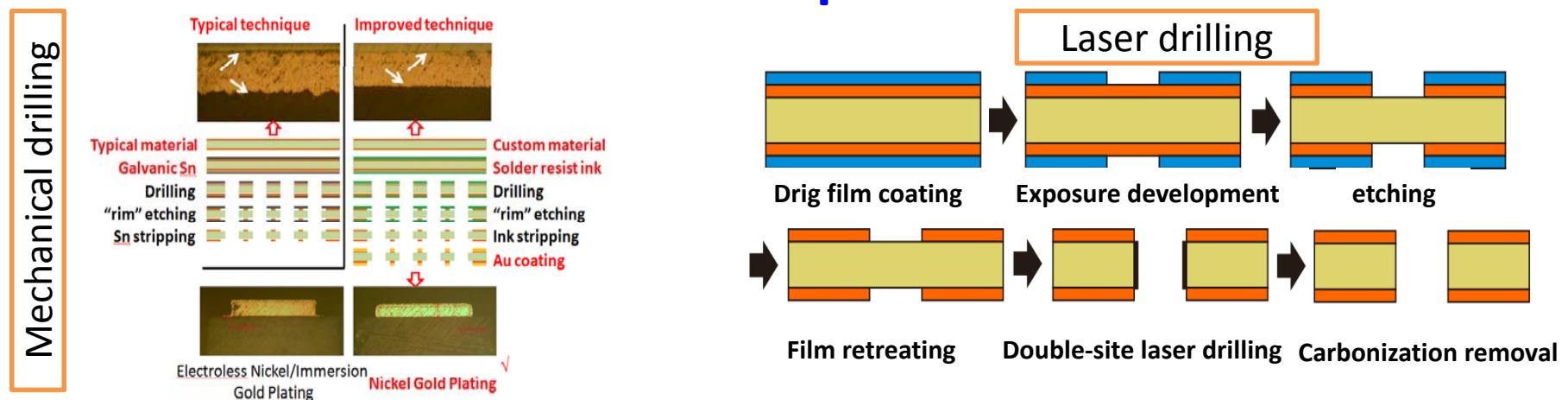


Low neutron absorption
and scattering
Low radioactivity



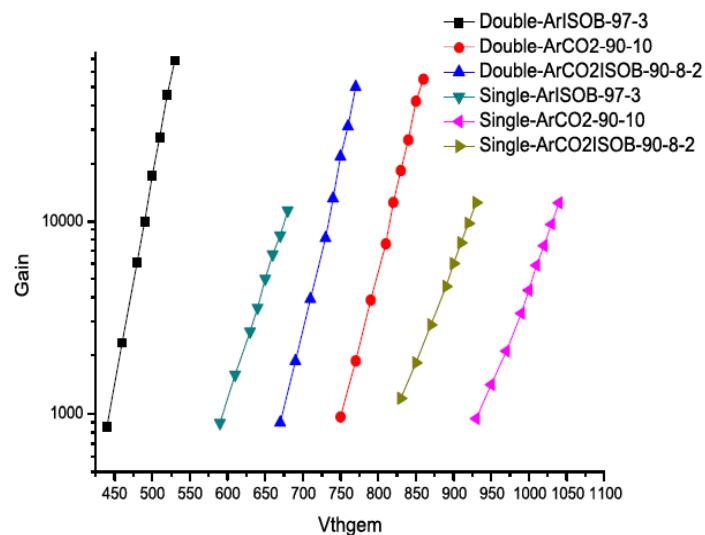
Resistive THGEM
Well THGEM
Groove THGEM
Multi-layer THGEM
...

Production and performance

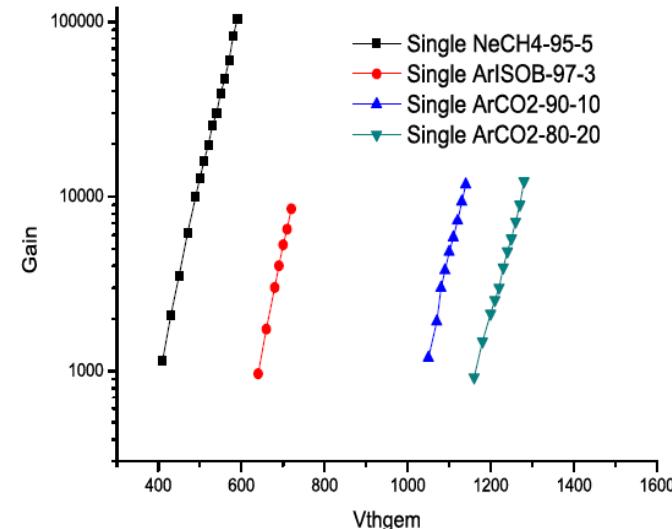


| Substrate | FR-4 | Ceramic | PTFE (Teflon) | Kapton (PI) |
|--|---------------|---------------|-----------------|------------------|
| Mechanical properties | rigid & tough | fragile | tough, flexible | toughn, flexible |
| Cost | Cheap | High | High | High |
| Regular performance: Ar+IsoB: 97-3, 120h test | | | | |
| Withstand voltage (in air) /V | 1400 | 1200 | 1800 | 1600 |
| Gain of single layer | 8000 | 5000 | 10000 | 10000 |
| Stability | Good | normal | Good | Good |
| Big-area detector/m^2 | OK | - | OK | OK |
| Substrate | S-Area/m^2 | HD/mm | Pitch/mm | TH/mm |
| FR-4 | <=0.5*1.0 | 0.10~0.5(0.2) | >=0.3 (0.6) | 0.1~0.3(0.2) |
| Kapton | <=0.5*1.0 | 0.10~0.5(0.2) | >=0.3 (0.6) | 0.05~0.3(0.2) |
| Ceramic | <=0.5*0.5 | 0.15~0.5(0.2) | >=0.4 (0.6) | 0.1~0.3(0.2) |
| PTFE (Teflon) | <=0.5*1.0 | 0.15~0.5(0.2) | >=0.4 (0.6) | 0.1~0.3(0.2) |

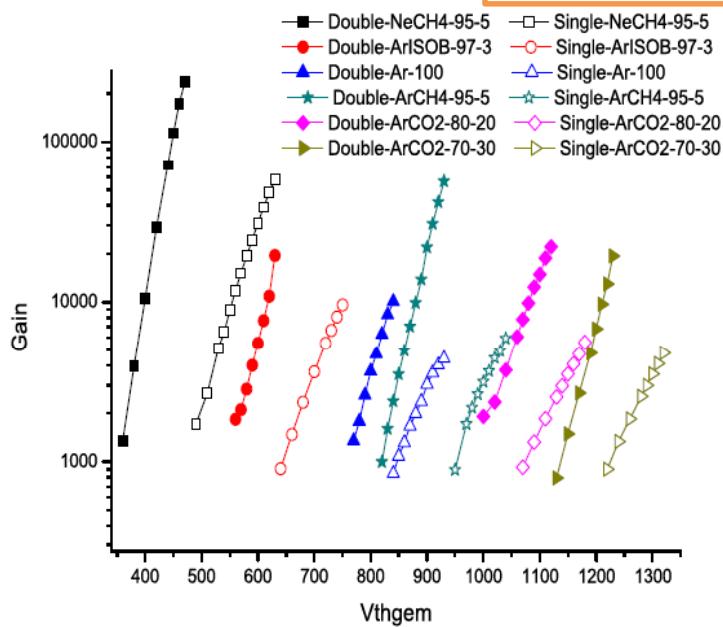
FR-4



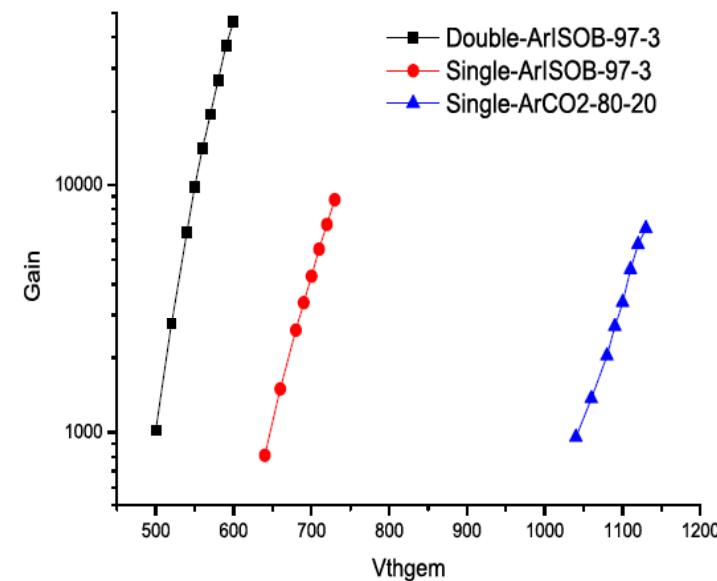
Ceramic



PTFE

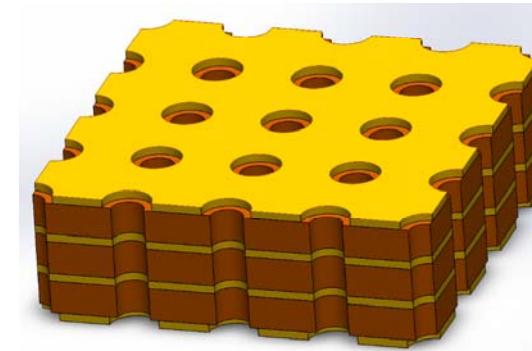
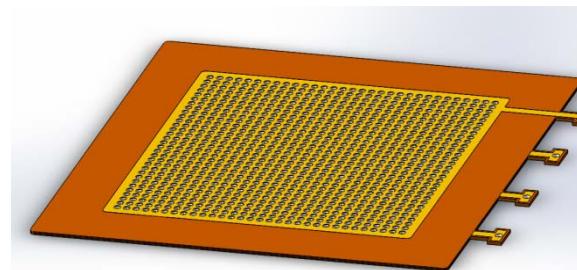
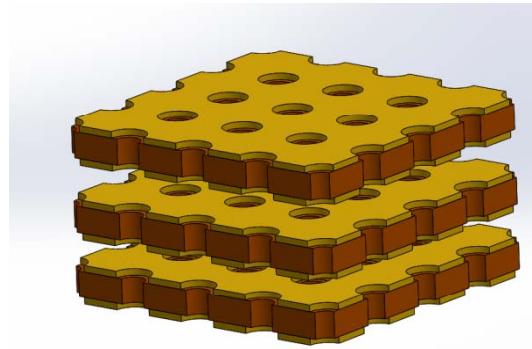
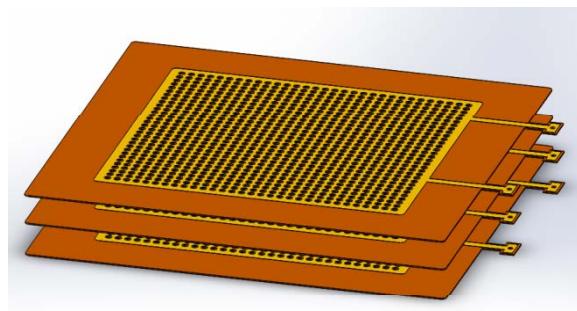


Kapton

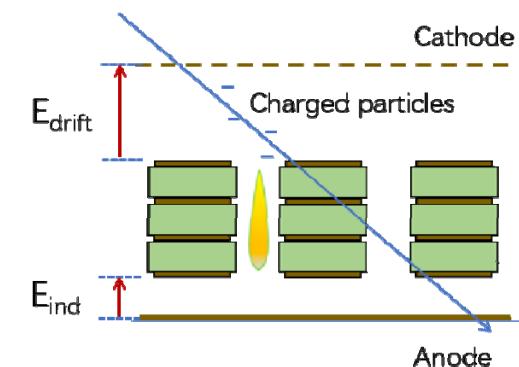
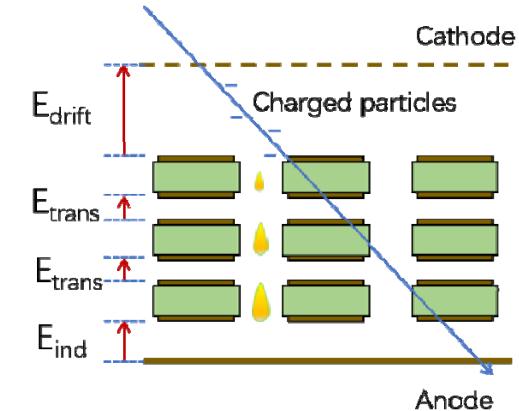


M-THGEM: a novel structure

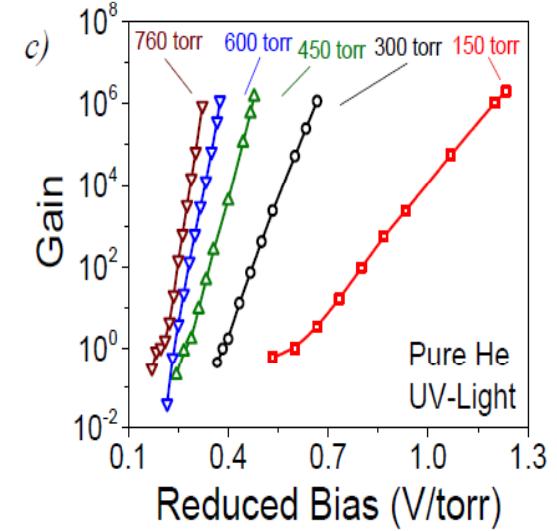
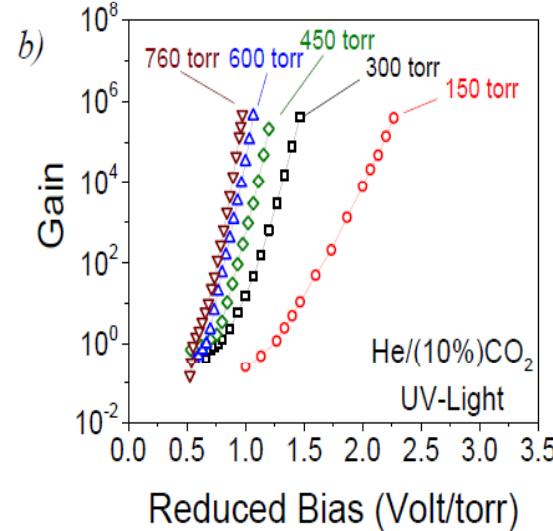
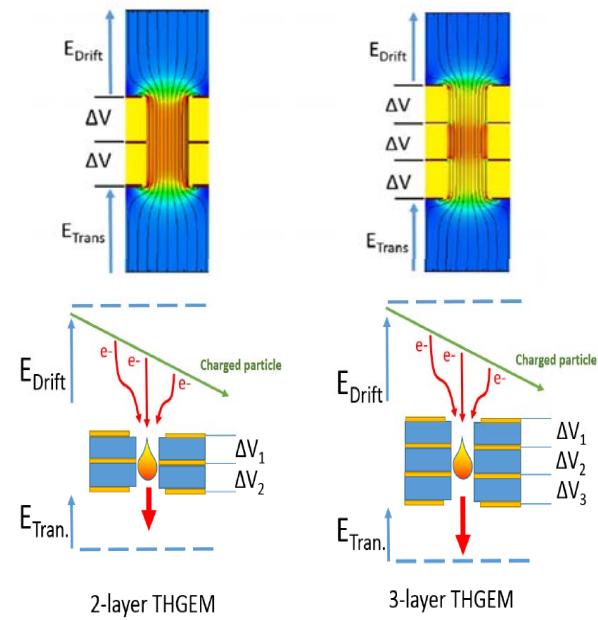
Multi-layer THGEM (M-THGEM) was proposed by M. Cortesi in Ref[1]. It is a new structure to reach smaller thickness, more compact structure, better performance and stability. M-THGEM is produced based on the multi-layer PCB technology by mechanical drilling and chemical etching.



Multi-layer PCB + Mechanical drilling + rim etching



Advantages



Structure:

- Single film, multi-layer successive avalanche, no transfer gaps;
- No parallelism problem for layers and no concentricity problem for holes;
- The thickness and types of substrate are selectable, 0.2, 0.25, 0.3, 0.4/layer ;
FR4, PI, Ceramic and PTFE, all substrate can be chosen for M-THGEM.

Production:

At least a half of mechanical drilling time is saved, very important for mass production.

Performance:

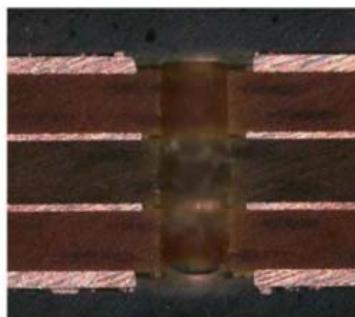
High gain, more stable

Stable operation in various gas mixtures even pure noble gas (He/Ne/Ar/Xe)

Good gain character in a wide range of gas pressures (150~760 torr)

Development

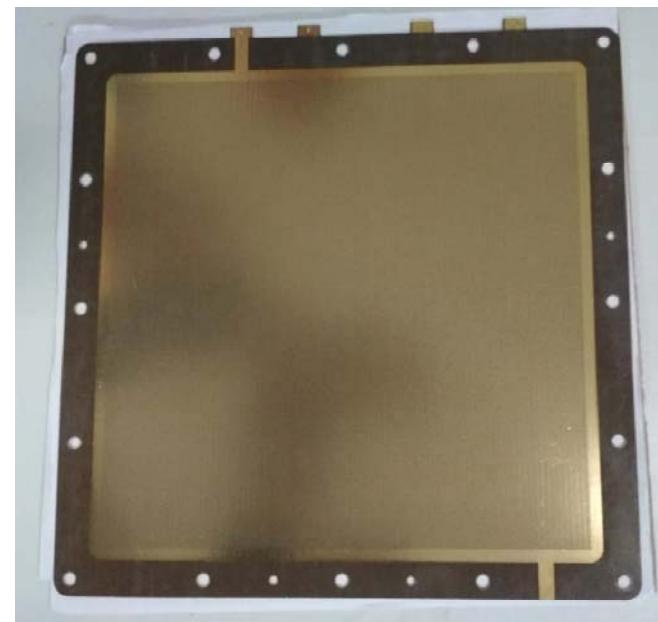
Based on the mature THGEM production techniques developed by IHEP and KingBrother Co. Ltd., M-THGEMs with various substrates, layers and dimensions were produced.



HD: 200 μ m
Pitch: 600 μ m
Rim: 80 μ m

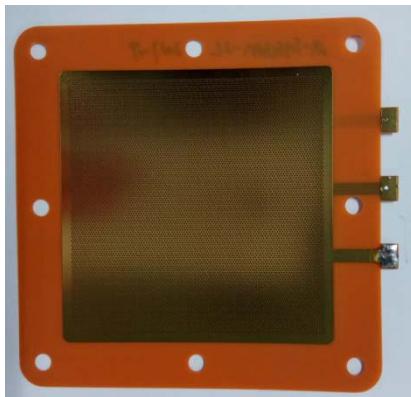
Total thickness:
2L: 300 μ m
3L: 500 μ m

PTFE, 200×200 mm²

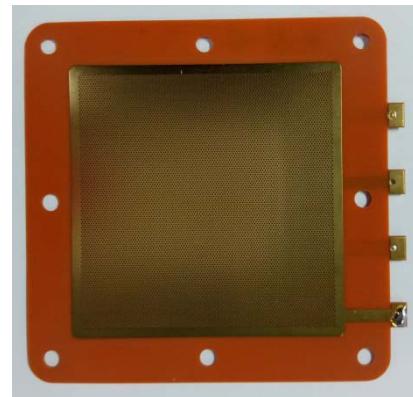


Cross sections of 2L(left) and 3L(right)M-THGEMs

FR-4 and PI, 60×60 mm²



2-layer M-THGEM

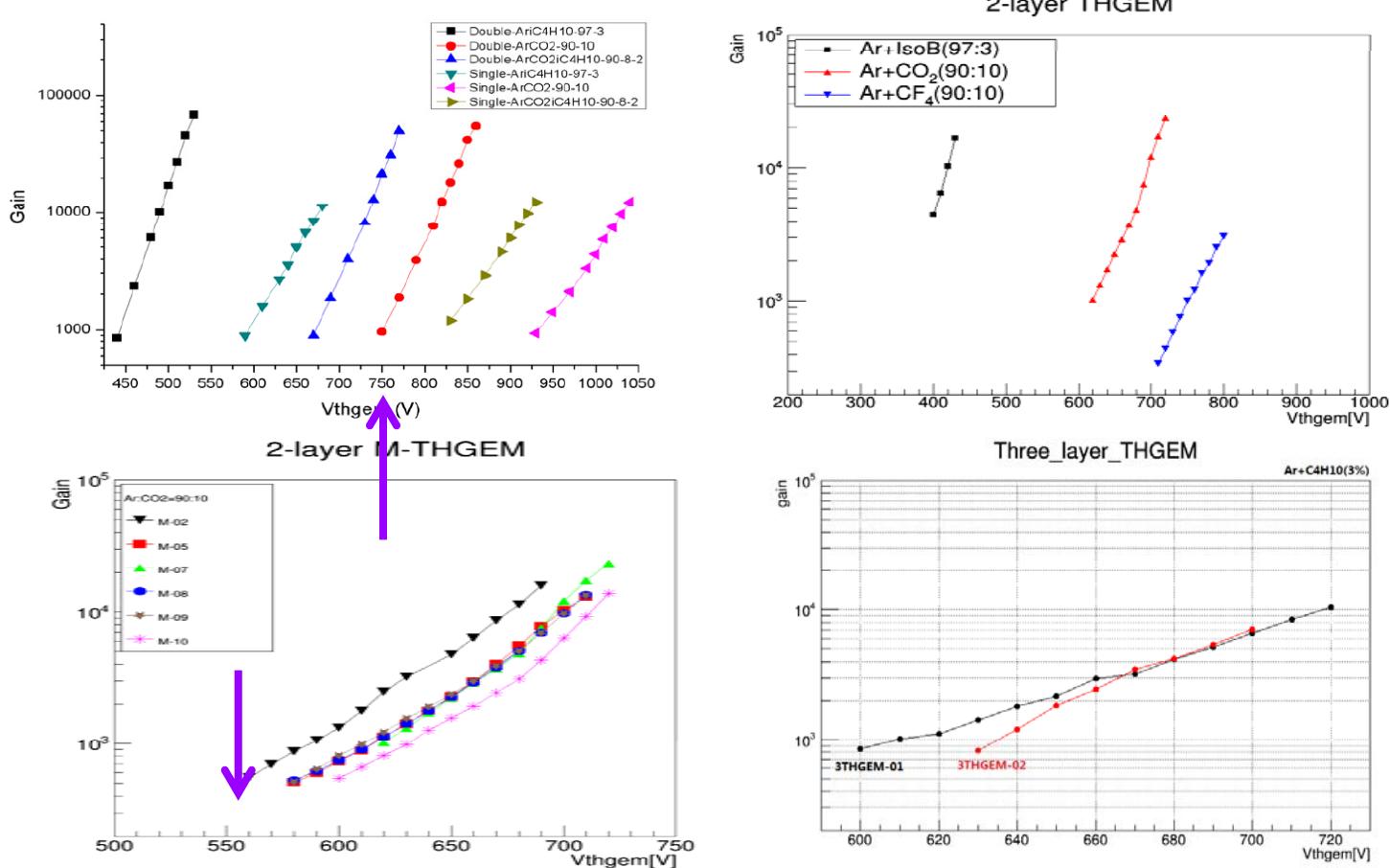


3-layer M-THGEM

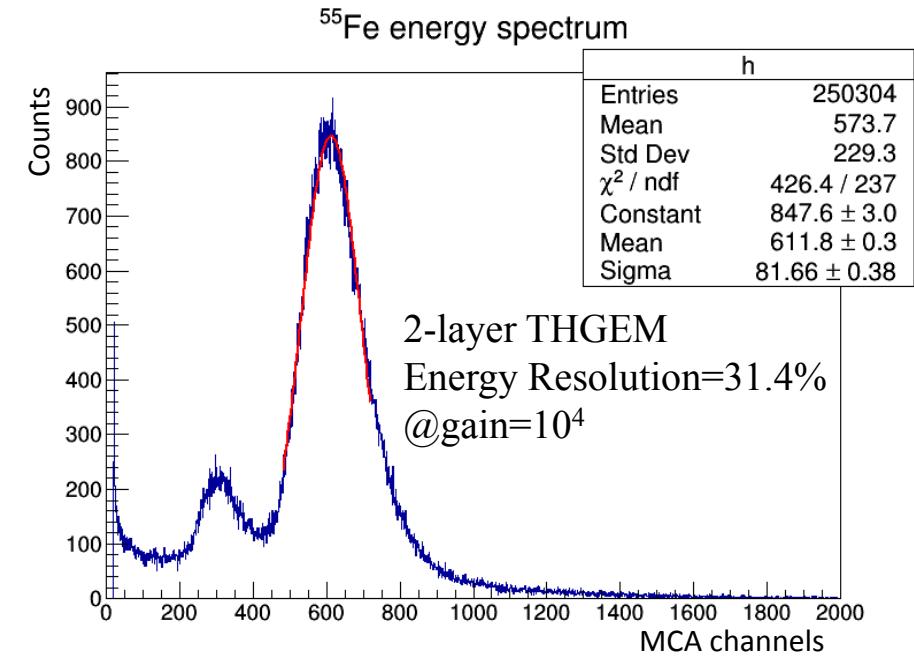
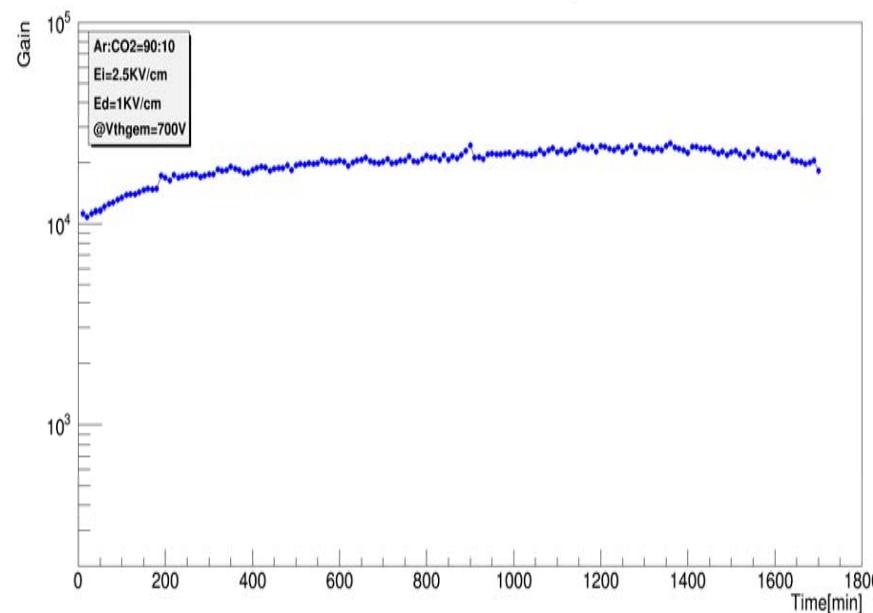
3-layer M-THGEM

Ceramic M-THGEMs were also produced and provided for users in USA and Italy. ¹²

Performance



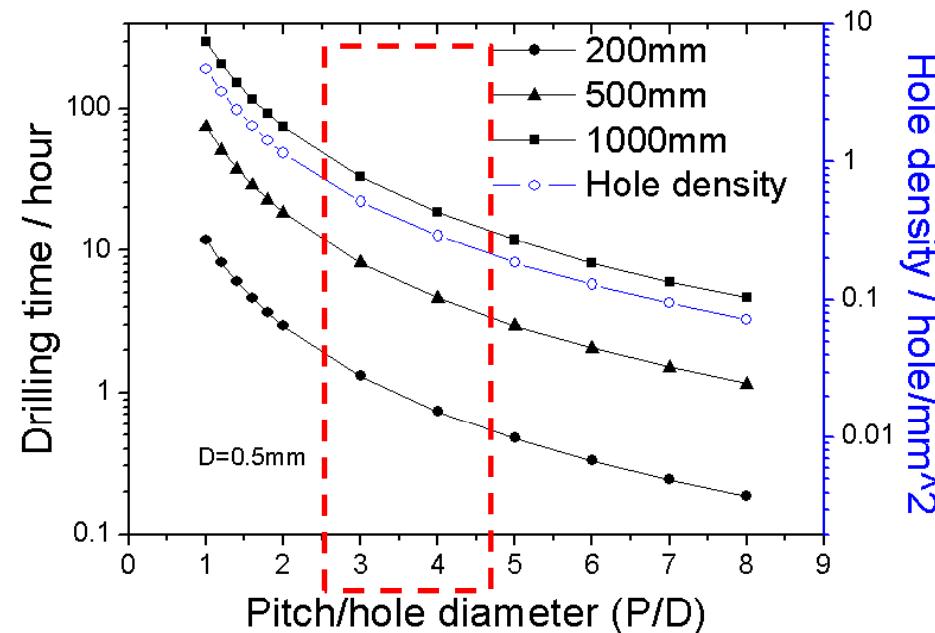
- Up to 1×10^4 high gain in typical gas mixtures, such as Ar+CO₂, Ar+iC₄H₁₀, and about 5000 in Ar+CF₄(carbon tetrafluoride).
- Lower operating voltage than the same number of layers cascade structure, about 150V.
- Three-layer M-THGEM shows similar gain level in 760 torr with two-layer M-THGEM, so it indicates that tow-layer M-THGEM is a better choice for normal applications. Three-layer M-THGEM has advantages in case of low gas pressure.



Good gain stability: 12% @ 2×10^4 , energy resolution is about 31%@ gain= 1×10^4 (Ar/CO₂=90:10) and will be better at lower gain.

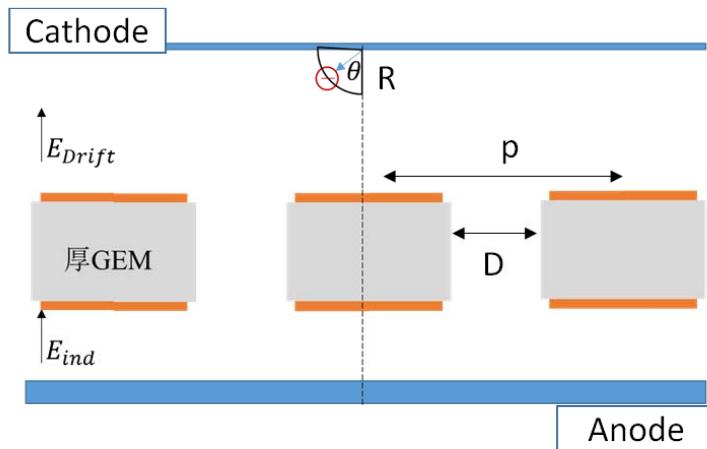
Big area

Besides the performance, the big area and mass production are two key factors for THGEM applications in HCAL and muon system. So far, mechanical drilling is still the only mature way to produce big area THGEM, therefore the size of THGEM is limited by **the width of PCB production line** and **the dimension of the numerical control drilling machine**. Reachable max size is $1.2 \times 0.5 \text{m}^2$ 。 In fact, the greatest difficulty of THGEM mass production is the huge time-consuming hole drilling.

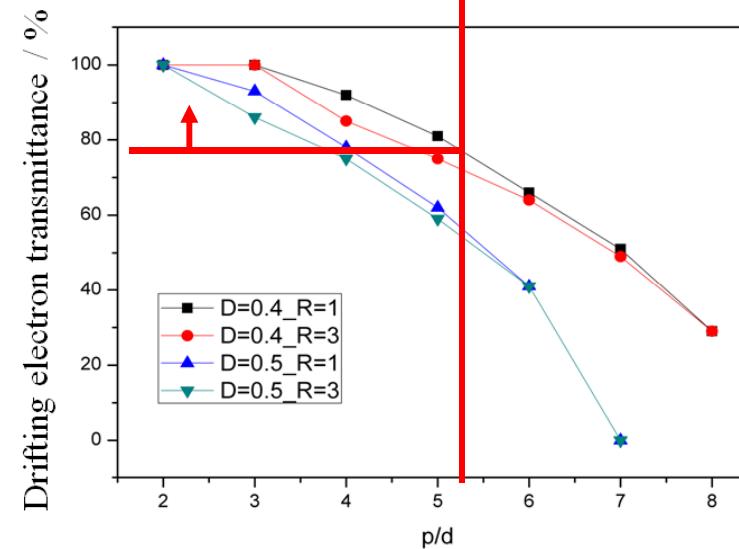
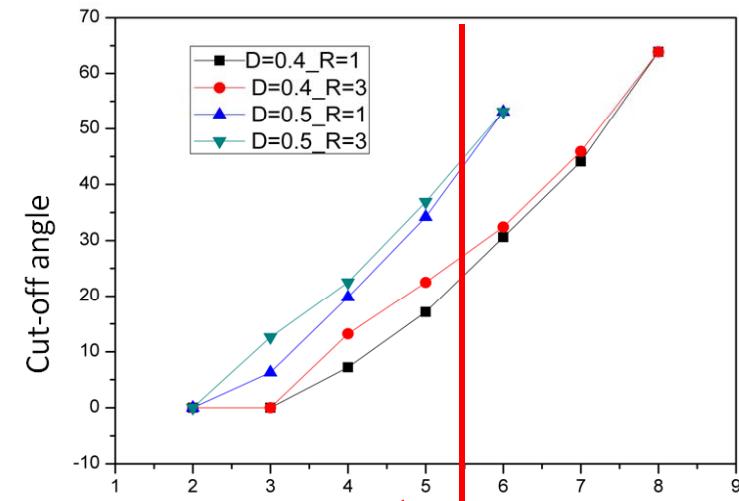


One of the effective way to reach big area for mechanical drilling is to reduce the total hole number, i.e., the hole density. The required spatial resolution for HCAL and muon system is about 1mm, which allows a larger hole pitch, and so lower hole density.

P/D optimization (Garfield++)



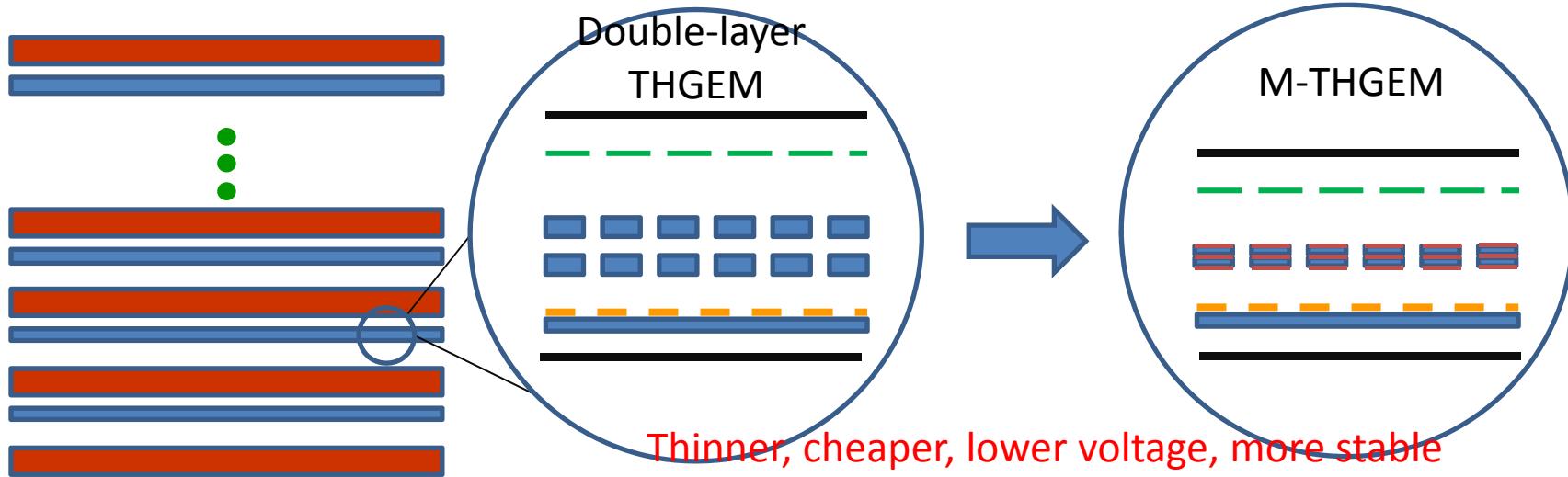
P/D: hole pitch over hole diameter;
 Cut-off angle: the minimum ejection angle for electron drifting into hole. Zero is vertical to the THGEM.
 Drifting electron transmittance: the ratio of electrons drifting over going into hole



For D=0.4mm, the largest P/D could be accepted is 5, and for D=0.5mm, P/D is ≤ 4 ; So the maximum pitch must be $\leq 2.0\text{mm}$. In this case, it takes about 18 hours to drill holes of a 1.0m^2 M-THGEM.

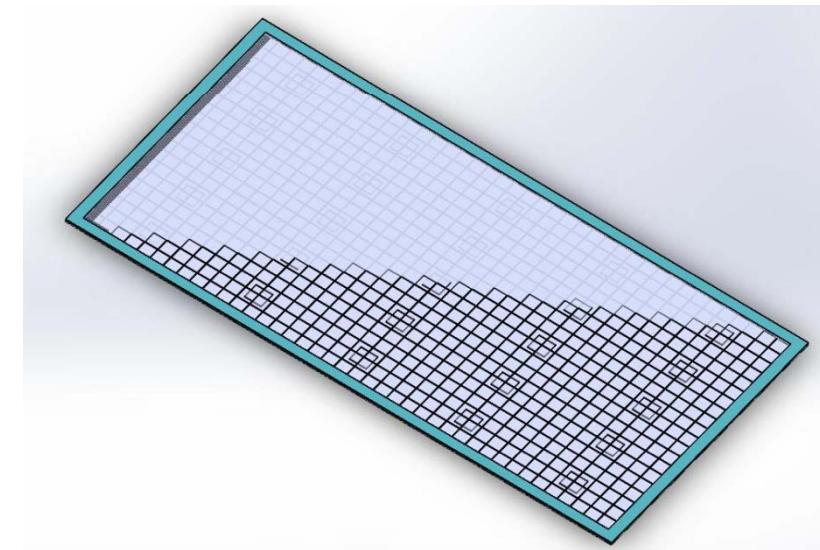
A prototype design for DHCAL and muon chamber

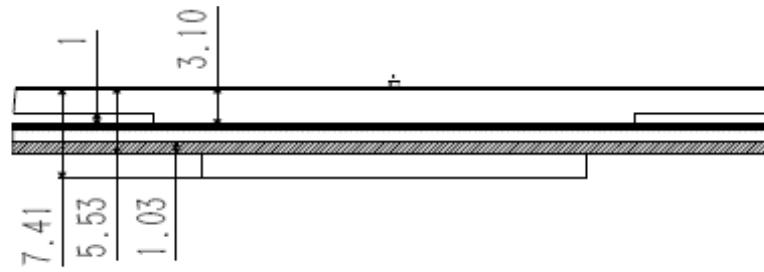
DHCAL/Muon system



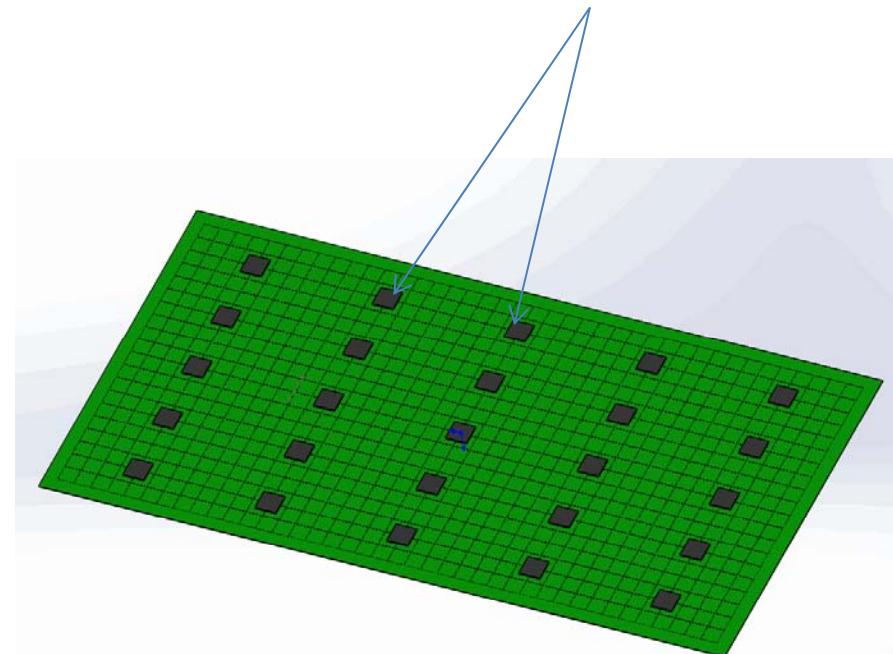
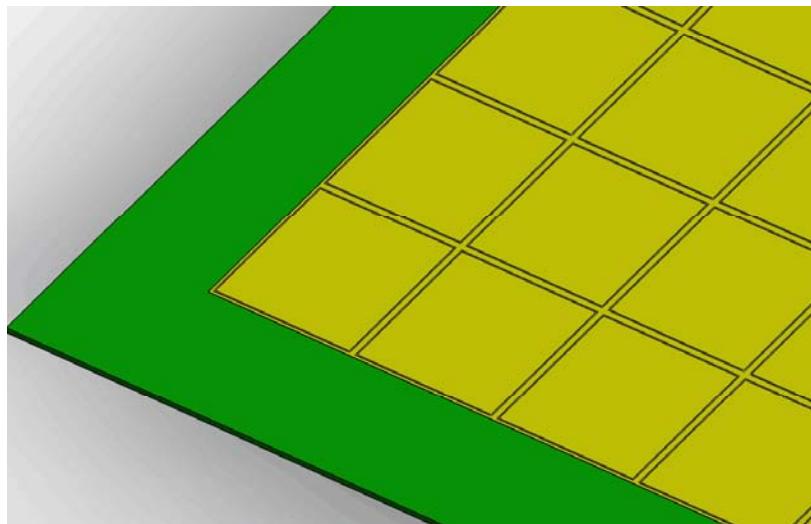
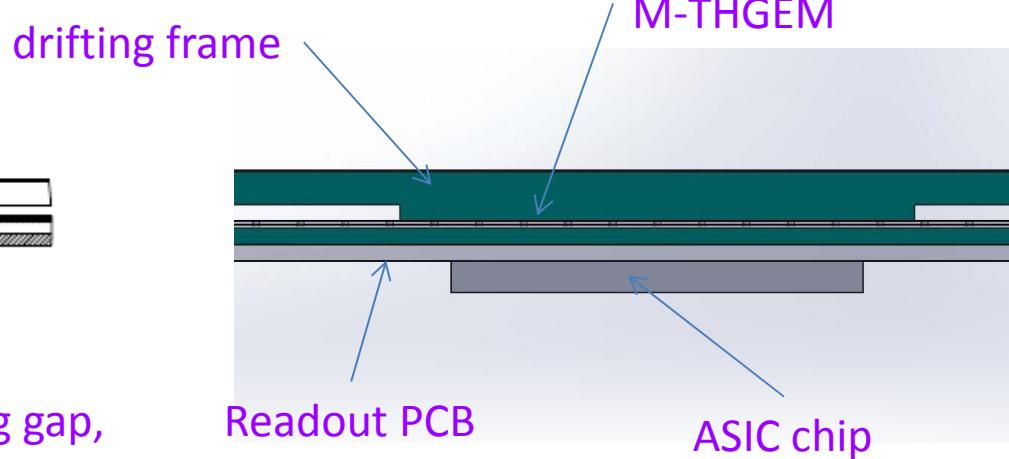
The modules of both DHCAL and muon system could have the similar structure, the main difference is the readout, one is PAD, and the other is strip.

A example of a $1.0 \times 0.5 \text{ m}^2$ module with 2.5-cm cell size





3-mm drifting gas gap, 1-mm inducing gap,
1.5-mm thick readout PCB board,
2-mm ASIC chip and electronic component.

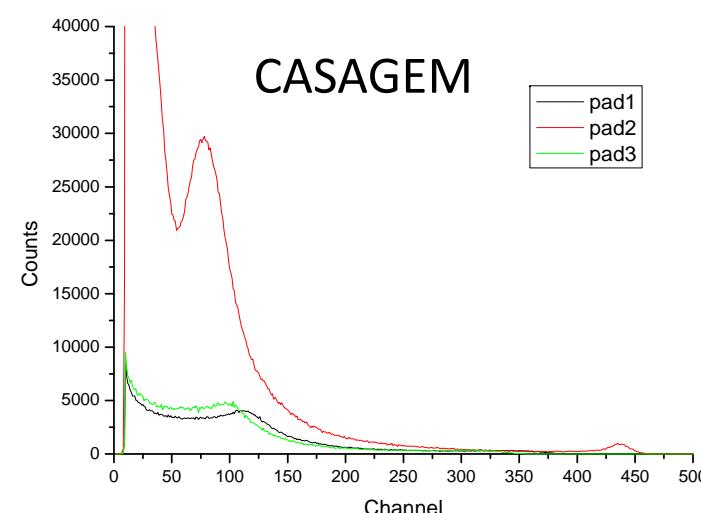
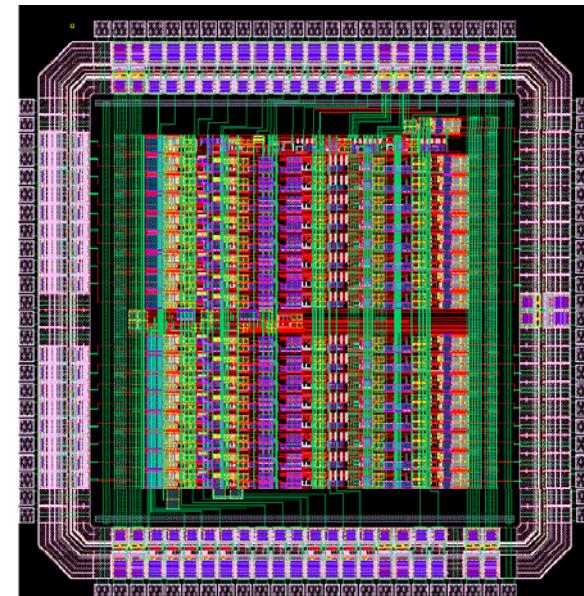
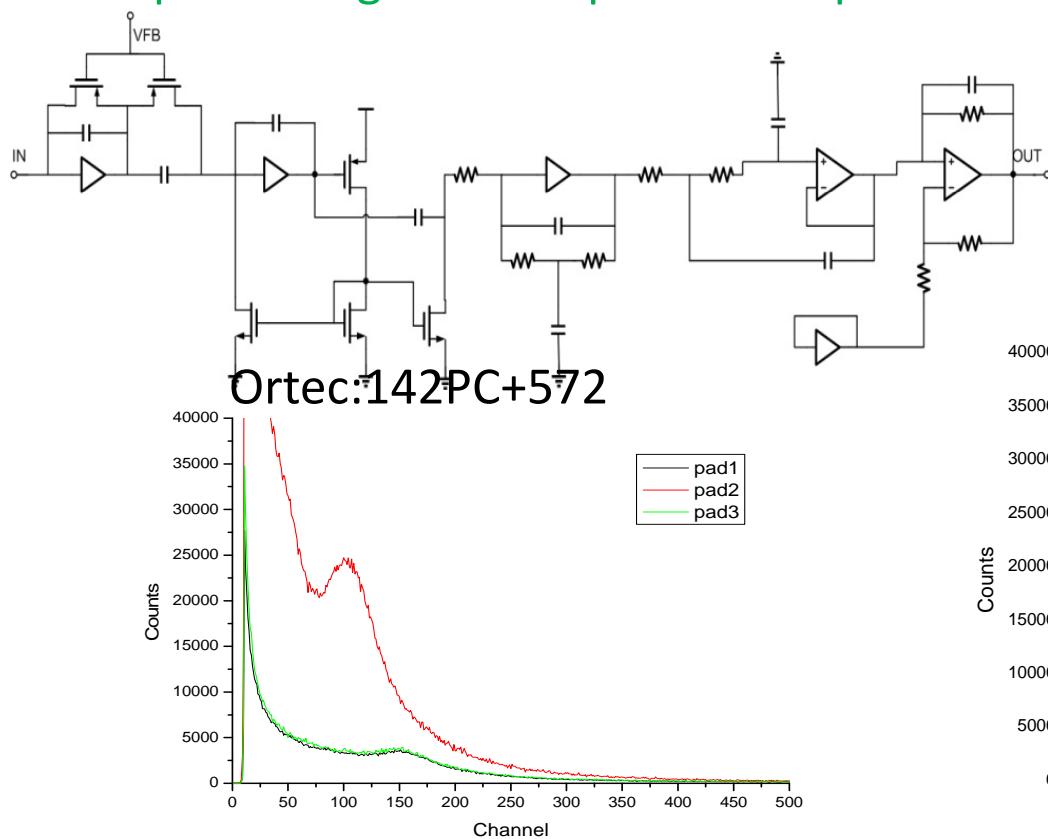


For HCAL, 2.5 mm readout PAD, $40 \times 20 = 800$ channels, adopting 32ch ASIC chip, each 8*4 cell array as an ASIC chip readout, 25 chips / module. For muon system, 40+20-60 channels /module, 2chips/module.

Front-end electronics

- Front-end electronics, homemade ASIC chips
CASAGEM, Tsinghua University, 32ch/chip version

- Structure: preAmp + 5 trends shaping
- Gain: 2mV/fC, 4mV/fC, 20mV/fC, 40mV/fC
- Shaping time: 20ns、40ns、60ns、80ns
- Channel: 32+1(1 trigger)
- Output: Single-ended parallel output



Summary

1. Various types of THGEMs had been developed in IHEP, CAS, Beijing China. Around THGEM applications, some achievements had been made, including: new substrate THGEMs, high spatial resolution THGEMs, big-area THGEMs, and new structure M-THGEM, etc.
2. M-THGEM is a new structure and promising THGEM and a high-rate, robust, compact and economical candidate for HCAL and muon system.
3. One way to reach big area and reduce huge time-consuming in hole drilling is to choose larger P/D, which could ensure the required spatial resolution and also the electron transmittance.
4. A prototype design is proposed for the modules of HCAL and muon system, module of $1.0 \times 0.5 \text{m}^2$ with 2.5-cm cell size, 25 ASIC chips and 800-channel PAD readout or 60-channel strip readout is recommended .
5. An electronics solution based on self-develop ASIC chip is also proposed for further development.

Thank you for attention!